

MBD54DWT1G

Preferred Device

Dual Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

Features

- Extremely Fast Switching Speed
- Low Forward Voltage – 0.35 V @ $I_F = 10$ mA
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



ON Semiconductor®

<http://onsemi.com>

30 VOLTS DUAL HOT-CARRIER DETECTOR AND SWITCHING DIODES

Anode 1 —————> 6 Cathode

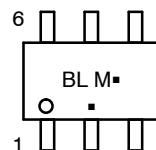
N/C 2 ○ ○ 5 N/C

Cathode 3 —————< 4 Anode

MARKING DIAGRAM



SOT-363
CASE 419B
STYLE 6



M = Date Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|------------|----------------------|-----------------------|
| MBD54DWT1G | SOT-363 (Pb-Free) | 3000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MBD54DWT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|--------------------|-----|------|------|---------------------------|
| Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$) | $V_{(\text{BR})R}$ | 30 | — | — | V |
| Total Capacitance ($V_R = 1.0 \text{ V}$, $f = 1.0 \text{ MHz}$) | C_T | — | 7.6 | 10 | pF |
| Reverse Leakage ($V_R = 25 \text{ V}$) | I_R | — | 0.5 | 2.0 | μA_{dc} |
| Forward Voltage ($I_F = 0.1 \text{ mA}_{\text{dc}}$) | V_F | — | 0.22 | 0.24 | Vdc |
| Forward Voltage ($I_F = 30 \text{ mA}_{\text{dc}}$) | V_F | — | 0.41 | 0.5 | Vdc |
| Forward Voltage ($I_F = 100 \text{ mA}_{\text{dc}}$) | V_F | — | 0.52 | 1.0 | Vdc |
| Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}_{\text{dc}}$, $I_{R(\text{REC})} = 1.0 \text{ mA}_{\text{dc}}$ (Figure 1)) | t_{rr} | — | — | 5.0 | ns |
| Forward Voltage ($I_F = 1.0 \text{ mA}_{\text{dc}}$) | V_F | — | 0.29 | 0.32 | Vdc |
| Forward Voltage ($I_F = 10 \text{ mA}_{\text{dc}}$) | V_F | — | 0.35 | 0.40 | Vdc |
| Forward Current (DC) | I_F | — | — | 200 | mA_{dc} |
| Repetitive Peak Forward Current | I_{FRM} | — | — | 300 | mA_{dc} |
| Non-Repetitive Peak Forward Current ($t < 1.0 \text{ s}$) | I_{FSM} | — | — | 600 | mA_{dc} |

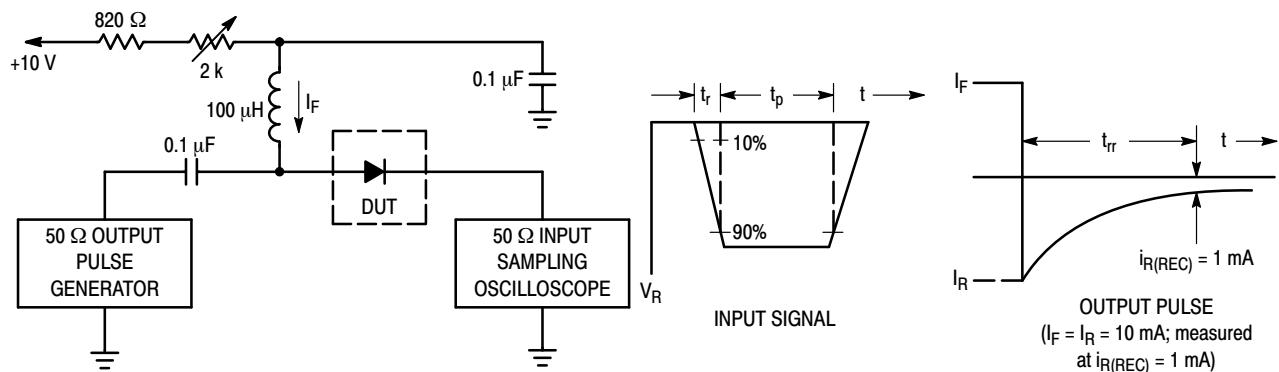


Figure 1. Recovery Time Equivalent Test Circuit

MBD54DWT1G

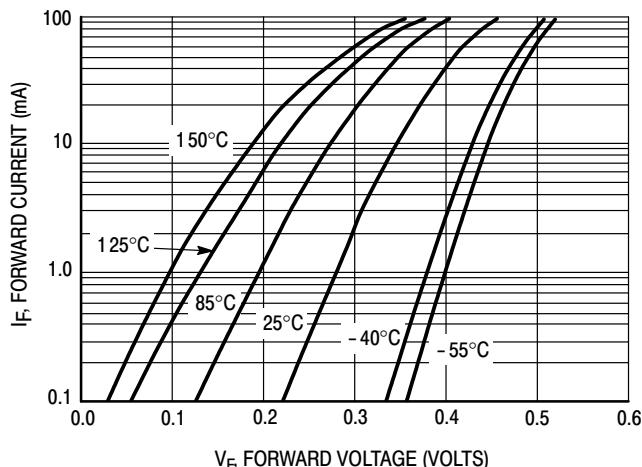


Figure 2. Forward Voltage

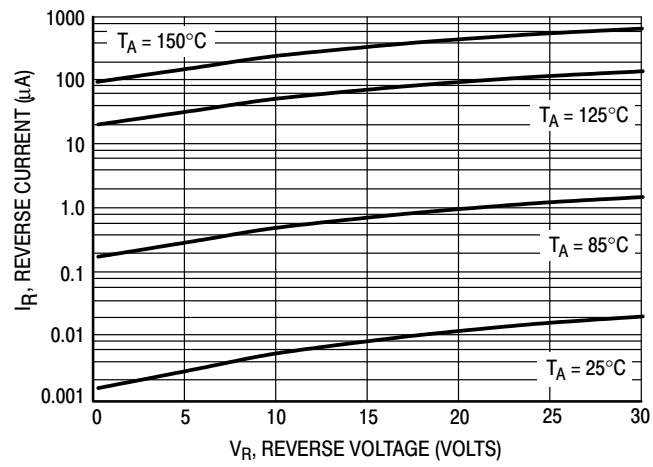


Figure 3. Leakage Current

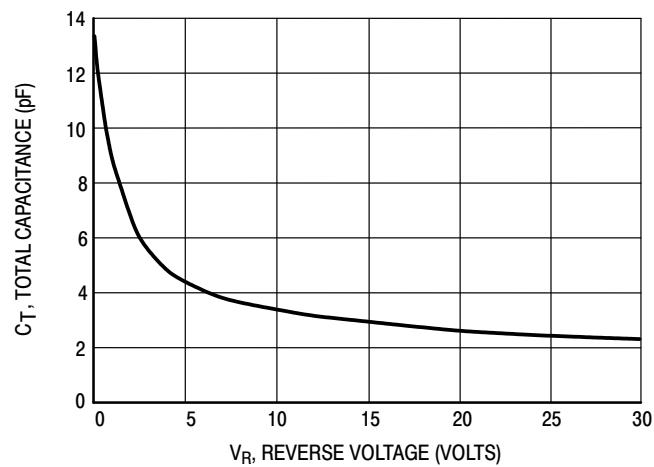
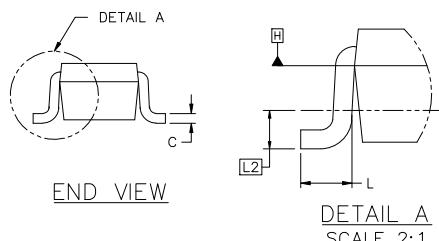
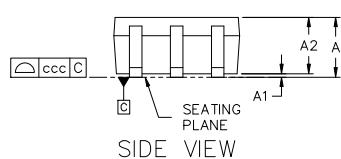
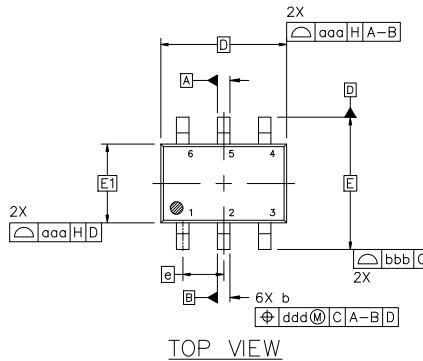


Figure 4. Total Capacitance



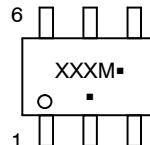
SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024



| DIM | MILLIMETERS | | |
|-----|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | --- | --- | 1.10 |
| A1 | 0.00 | --- | 0.10 |
| A2 | 0.70 | 0.90 | 1.00 |
| b | 0.15 | 0.20 | 0.25 |
| c | 0.08 | 0.15 | 0.22 |
| D | 2.00 | BSC | |
| E | 2.10 | BSC | |
| E1 | 1.25 | BSC | |
| e | 0.65 | BSC | |
| L | 0.26 | 0.36 | 0.46 |
| L2 | 0.15 | BSC | |
| aaa | 0.15 | | |
| bbb | 0.30 | | |
| ccc | 0.10 | | |
| ddd | 0.10 | | |

**GENERIC
MARKING DIAGRAM***



XXX = Specific Device Code

M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

| | | |
|------------------|-----------------------------|---|
| DOCUMENT NUMBER: | 98ASB42985B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION: | SC-88 2.00x1.25x0.90, 0.65P | PAGE 1 OF 2 |

onsemi and **onsemi**TM are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

SC-88 2.00x1.25x0.90, 0.65P

CASE 419B-02

ISSUE Z

DATE 18 APR 2024

| | | | | | |
|--|--|---|---|---|---|
| STYLE 1: PIN 1. Emitter 2 2. Base 2 3. Collector 1 4. Emitter 1 5. Base 1 6. Collector 2 | STYLE 2: Cancelled | STYLE 3: Cancelled | STYLE 4: PIN 1. Cathode 2. Cathode 3. Collector 4. Emitter 5. Base 6. Anode | STYLE 5: PIN 1. Anode 2. Anode 3. Collector 4. Emitter 5. Base 6. Cathode | STYLE 6: PIN 1. Anode 2 2. N/C 3. Cathode 1 4. Anode 1 5. N/C 6. Cathode 2 |
| STYLE 7: PIN 1. Source 2 2. Drain 2 3. Gate 1 4. Source 1 5. Drain 1 6. Gate 2 | STYLE 8: Cancelled | STYLE 9: PIN 1. Emitter 2 2. Emitter 1 3. Collector 1 4. Base 1 5. Base 2 6. Collector 2 | STYLE 10: PIN 1. Source 2 2. Source 1 3. Gate 1 4. Drain 1 5. Drain 2 6. Gate 2 | STYLE 11: PIN 1. Cathode 2 2. Cathode 2 3. Anode 1 4. Cathode 1 5. Cathode 1 6. Anode 2 | STYLE 12: PIN 1. Anode 2 2. Anode 2 3. Cathode 1 4. Anode 1 5. Anode 1 6. Cathode 2 |
| STYLE 13: PIN 1. Anode 2. N/C 3. Collector 4. Emitter 5. Base 6. Cathode | STYLE 14: PIN 1. Vref 2. GND 3. GND 4. Iout 5. Ven 6. Vcc | STYLE 15: PIN 1. Anode 1 2. Anode 2 3. Anode 3 4. Cathode 3 5. Cathode 2 6. Cathode 1 | STYLE 16: PIN 1. Base 1 2. Emitter 2 3. Collector 2 4. Base 2 5. Emitter 1 6. Collector 1 | STYLE 17: PIN 1. Base 1 2. Emitter 1 3. Collector 2 4. Base 2 5. Emitter 2 6. Collector 1 | STYLE 18: PIN 1. Vin1 2. Vcc 3. Vout2 4. Vin2 5. Gnd 6. Vout1 |
| STYLE 19: PIN 1. Iout 2. Gnd 3. Gnd 4. Vcc 5. Ven 6. Vref | STYLE 20: PIN 1. Collector 2. Collector 3. Base 4. Emitter 5. Collector 6. Collector | STYLE 21: PIN 1. Anode 1 2. N/C 3. Anode 2 4. Cathode 2 5. N/C 6. Cathode 1 | STYLE 22: PIN 1. D1 (i) 2. Gnd 3. D2 (i) 4. D2 (c) 5. Vbus 6. D1 (c) | STYLE 23: PIN 1. Vn 2. Ch1 3. Vp 4. N/C 5. Ch2 6. N/C | STYLE 24: PIN 1. Cathode 2. Anode 3. Cathode 4. Cathode 5. Cathode 6. Cathode |
| STYLE 25: PIN 1. Base 1 2. Cathode 3. Collector 2 4. Base 2 5. Emitter 6. Collector 1 | STYLE 26: PIN 1. Source 1 2. Gate 1 3. Drain 2 4. Source 2 5. Gate 2 6. Drain 1 | STYLE 27: PIN 1. Base 2 2. Base 1 3. Collector 1 4. Emitter 1 5. Emitter 2 6. Collector 2 | STYLE 28: PIN 1. Drain 2. Drain 3. Gate 4. Source 5. Drain 6. Drain | STYLE 29: PIN 1. Anode 2. Anode 3. Collector 4. Emitter 5. Base/Anode 6. Cathode | STYLE 30: PIN 1. Source 1 2. Drain 2 3. Drain 2 4. Source 2 5. Gate 1 6. Drain 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

| | | |
|------------------|-----------------------------|---|
| DOCUMENT NUMBER: | 98ASB42985B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| DESCRIPTION: | SC-88 2.00x1.25x0.90, 0.65P | PAGE 2 OF 2 |

onsemi and **ONSEMI** are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, **ONSEMI**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales

